



conducting gates of the switching transistor, the source of band control voltage being connected to a dividing point of the resistance, and the conducting drain and source nodes of the switching transistor being in series connection with the second impedance element to open-circuit the second impedance element.

7. A dual band RF tuning circuit as recited in claim 6, wherein the first and second impedance elements are capacitance impedance elements.

8. A dual band RF tuning circuit as recited in claim 6, wherein the voltage divider has a current blocking resistance in parallel connection with the conducting drain and source nodes of the switching transistor, and the source of band control voltage is connected through a resistor to a dividing point of the current blocking resistance.

9. A dual band RF tuning circuit comprising:  
a first inductance impedance element and a second inductance impedance element between an RF input port and an RF output port,

the tuning circuit being tuned by the first and second inductance impedance elements to receive a first RF signal and to provide the first RF signal at the output port,

the tuning circuit being tuned by the first inductance impedance element alone to receive a second RF signal and to provide the second RF signal at the output port,

a switching transistor being switched on and off by changing its bias voltage,

a band control voltage source connected to the switching transistor to change its bias voltage,

the switching transistor having conducting drain and source nodes connected to the second inductance impedance element to short the second inductance impedance element, which tunes the tuning circuit by the first inductance impedance element,



